Case No. 10519/37

DECLARATION FOR PATENT APPLICATION

As a below named inventor hereby declare that:

JAN 2 4 2002

My residence, post office address and citizenship are as stated below next to my name.

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled WRITE-MANY MEMORY DEVICE AND METHOD FOR LIMITING A NUMBER OF WRITES TO THE WRITE-MANY MEMORY DEVICE, the specification of which:

WRITE-MANY M specification of v		DD FOR LIMITING A NUMBER OF WRI	ITES TO THE WRITE-MAN	Y MEMORY DEV	ice, the
— —	is attached hereto.				
_					
	was filed on October 5, 2001 as Application Serial No. 09/972,787.				
	and was amended on				
	at I have reviewed and und amendment referred to abov	erstand the contents of the above-ive.	identified specification, i	including the cla	ilms, as
I acknowledge tl Regulations, § 1.		tion which is material to the paten	tability as defined in Ti	tle 37, Code of	Federal
inventor's certifi United States, lis	cate or § 365(a) of any PC ted below and have also ide	der 35 U.S.C. § 119(a)-(d) or § 36. T International application which entified below, by checking the box having a filing date before that of the	designated at least one, any foreign application	country other to for patent or in	han the ventor's
Prior Foreign Ap	plication(s)			Priority Clair	med
(Number)	(Country)	(Day/Month/Ye	ear Filed)	Yes	No
I hereby claim th	e benefit under 35 U.S.C. §	119(e) of any United States provision	onal application(s) listed	below:	
(Applica	tion Serial No.)	(Filing Date)	. <u></u>		
application designs is not disclosed in U.S.C. § 112, I a	nating the United States, lis n the prior United States or acknowledge the duty to di	§ 120 of any United States applicated below and, insofar as the subject PCT International application in the sclose information which is material late of the prior application and the	et matter of each of the cl the manner provided by t al to patentability as de	laims of this app he first paragrap fined in 37 CFR	olication oh of 35 R § 1.56
(Applica	tion Serial No.)	(Filing Date)	(Status-patented	l, pending, abanc	doned)
belief are believe the like so made that such willful Inventor's Signat	ed to be true; and further the are punishable by fine or in false statements may jeopar ure e or first inventor	rein of my own knowledge are true at these statements were made with apprisonment, or both, under Section dize the validity of the application of DAVID R. FRIEDMAN MENLO PARK, CALIFORNIA UNITED STATES OF AMERICA 267 Hedge Road, Menlo Park, Ca	the knowledge that will a 1001 of Title 18 of the any patent issued there Date:	ful false stateme United States C	ents and
				•	

Case No. <u>10519/37</u>

Date:

Inventor's Signature

Full name of second joint inventor, if any

Residence

Citizenship

Post Office Address

J. JAMES TRINGAVI

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UNITED STATES OF AMERICA

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